Simple wideband linear voltage-to-frequency converter

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A pulse generator is described which has a voltage-controlled frequency continuously variable over more than three decades; the control function is linear and independent of supplyvoltage changes, and the control sensitivity is stable, independent of transistor characteristics and easily adjustable.

Es wird ein spannungsgeregelter Impulsgenerator beschrieben, dessen Frequenz über mehr als drei Dekaden stetig einstellbar ist. Die Einstellung ist linear und unabhängig von Schwankungen der Versorgungsspannung. Die Einstellempfindlichkeit ist konstant, unabhängig von den Transistorkennlinien und leicht abzugleichen.

Le générateur d'impulsions décrit dans cet article a une fréquence à tension contrôlée à variation continue sur plus de trois décades; la fonction de contrôle est linéaire et indépendante des changements de tension d'alimentation. La sensibilité de contrôle est stable, indépendante des caractéristiques de transistors et d'un réglage aisé.

THE CIRCUIT DIAGRAM of the converter is shown I in Fig. 1. The circuit is essentially a version of the conventional astable multivibrator, in which VT₁ and VT₂ are the main oscillating transistors. To ensure linear charging of the timing capacitors, the two charging resistors are replaced by two current sources utilizing transistors VT₃ and VT₄.² Transistors VT₅ and VT₆ are emitter followers for rapidly discharging the timing capacitors, hence extending the upper frequency limit. To render the frequency independent of the supply voltage and transistor-parameter variation, the voltage swing on the timing capacitors must be held constant. This is achieved by the use of MRZ₁ in connection with the fast silicon diodes $MR_{2,3,4,5}$; this arrangement also renders the voltage swing independent of temperature,

low potential; thus MR₄ is conducting and MR₅ and VT_6 are off. The current source VT_3 provides the base current for VT_2 , while the other current source VT_4 charges C_2 ; therefore the base potential of VT₁ rises linearly. When it reaches the cut-in voltage of VT_1 , this conducts, its collector voltage drops and the conventional regenerative action of the astable multivibrator takes place, turning VT₂ off. MR₅ and VT₆ conduct and take up the role of MR₃ and VT₅. C_2 is discharged through the small output resistance of VT_6 and the input resistance of VT₁. Now the current source VT₄ provides base current for VT_1 while VT_3 charges C_1 , and so on.

provided that the Zener diode is temperature-compensated.

Circuit function

Let VT_1 be off and VT_2 on; thus VT_1 collector is at a high potential, MR₂ is cut off, and MR₃ and VT₅ are conducting. VT₂ being saturated, its collector is held at a



Neglecting the saturation voltage of either VT₁ or VT₂ in comparison with the Zener voltage, it can be shown from the preceding description that the voltage swing at either base of the oscillating transistors is equal to the Zener voltage V_z . Hence, for a symmetrical circuit,



where $I = \text{current provided by each of the two current}}$ T = period of oscillation $C = \text{timing capacitance } (C_1 = C_2 = C)$ $V_z = \text{Zener voltage}$ The current I is given by $I = (V_x - V_B)/R$ (2) where $V_x = \text{control voltage}$ $R = \text{sensitivity resistor } (R_1 = R_2 = R)$ $V_B = e - b$ voltage of VT₃ and VT₄* Combining equations (1) and (2), the frequency of oscillation is given by $f = \frac{V_x - V_B}{2CRV_z}$ (3)

From which, the frequency sensitivity S (in Hz/V) is given



as

 $S = 1/2CRV_z \qquad (4)$

Therefore S is constant, independent of supply-voltage and transistor-parameter variations, and can be adjusted to the required value by adjusting R (here called the sensitivity resistor).

Design considerations and experimental results

It is appropriate at this point to discuss briefly the limitations imposed on the frequency range, together with the effect of changing various circuit parameters in an attempt to arrive at the optimum design. Experimental results are presented together with suggestions for waveform improvement and temperature stability. A method of direct digital control of frequency is also indicated.

(a) Frequency range

The minimum oscillating frequency is determined by the minimum base current required to drive VT_1 or VT_2 into saturation. Provided that the combined switching time of the transistors is small compared with the period of oscillation, the upper limit of the linear control function is imposed by the discharging time of the timing capacitors. If this exceeds the time of half a period, the timing capacitor will not be able to discharge completely, resulting in reduced voltage swing and deviation from linear control. It can be shown (see Appendix) that the frequency range (f.r.) is given by



Fig. 2 Measured control characteristics for (a) band 1 (10Hz-10kHz) (b) band 2 (7kHz-3·4MHz)

As both the upper and lower limits of the frequency range are set by the limited h_{FE} of both VT₁ and VT₂ and both VT₅ and VT₆ respectively, the frequency range can be extended by replacing any of these individual transistors by a Darlington-connected pair.

(b) Experimental results

Fig. 1 is a converter designed to operate in the band $10Hz \rightarrow 10kHz$ (1000:1). The measured control characteristic in Fig. 2 shows a frequency sensitivity of about 312Hz/V. Calculation from equation (4) would indicate a value of 318Hz/V. The characteristic has an offset of about 0.6V, which is the junction voltage of each of the current sources. This may be minimized by adding a diode, as shown in Fig. 3. As the offset varies with the current I, deviations from linearity result at low input voltages (Fig. 4). By including the circuit shown in Fig. 6, see (d), these deviations are completely eliminated. The same circuit with similar transistors is transformed to another frequency band by changing C and R_0 and adjusting R. Using the additional values given in Fig. 1, the oscillator covers the band 7kHz-3MHz, with measured characteristics as shown in Fig. 2. Here the upper frequency limit is set by the switching speed of the transistors used.

f.r. =
$$\frac{h_{\rm FE}^2}{x \ln [x/(x-1)]}$$
 (5)

where $h_{\rm FE}$ is the transistor d.c. current gain (assumed equal for all transistors) and $X = V_{\rm CC}/V_{\rm Z}$. Thus choosing transistors of high current gain widens the control range. There is also the possibility of using a value of x which gives an optimum frequency range; however, in choosing Vcc, one must consider other limitations, such as the breakdown of VT_1 or VT_2 , power consumption, proper operation of the Zener diode etc. It can also be shown that the absolute value of the frequency depends only on the time constant CR_c . Thus it may be seen that, for two reasons, a good choice is a combination of C rather large and $R_{\rm C}$ rather small. This derives from the fact that, if C is much larger than the storage-capacitive effects of the saturated transistor, the transistor does not impose any limit on the upper frequency range. A smaller value of R_c ensures working less deeply in saturation, thus allowing smaller storage times.

To simplify matters, assume that the voltage drop on all conducting silicon junctions is equal to $V_{\rm B}$ (which is approximately 0.7V).



Fig. 3 Minimizing characteristic offset by addition of diode MR_{\bullet}



The effect of power-supply variation is measured to be 5Hz/V for band I and 100Hz/V for band II. By replacing each of VT_5 and VT_6 by a Darlington-connected pair each, the upper frequency limit of band I is extended to about 50kHz, which results in a 50 000:1 control range. Similarly, if Darlington pairs are used to replace VT_1 or VT_2 , the lower limit extends to about 0.5Hz (instead of 10Hz).

(c) Output waveform

The pulses obtained are of 50% duty cycle and of very small falltime, but the risetime is large. Although one is not necessarily interested in the output waveform of the converter (as it may be a preliminary stage in a system), a reasonable waveform could be obtained by adding a transistor, as shown in Fig. 5, or by moreconventional means.



Fig. 6 Addition of four transistors provides complete temperature-independence and eliminates characteristic

(d) Temperature stability

As noted earlier, the four silicon diodes $MR_{2,3,4,5}$, together with MRZ_1 , connected as shown in Fig. 1, result in a constant voltage swing (equal to the Zener voltage) on either of the timing capacitors. This derives from the fact that the Zener maintains point P at a potential $(-V_{CC}+V_Z)$. In one state, VT_1 is conducting and diode MR_1 clamps

offset.

* Should have similar V_{b} and high h_{FE}

the capacitor terminal (marked X) at an approximate potential of $(-V_{CC}+V_B)$ (neglecting $V_{CE(Sat)}$); in the other state, VT₁ and MR₂ are cut off, and point X, is now clamped by MR₃ to a potential $(-V_{CC}+V_Z+V_B)$. Thus the voltage swing on the timing capacitor is V_Z . Thus frequency is made independent of supply voltage variations and, provided that the Zener is temperaturecompensated, the frequency is also made roughly independent of the temperature variation of either VT₁ or VT₂ or diode parameters.

The only remaining source of temperature instability is the variation in the e-b junction voltage of the current sources VT₃ and VT₄ with temperature. To compensate for this, the arrangement shown in Fig. 6 is suggested. The method consists essentially of holding the emitters of the two current sources almost at ground potential by lowering their bases with a junction drop. For best compensation, this junction must essentially carry an amount of current equal to that of the current sources. Transistor VT₇ is a current source to simulate the original current sources VT₃ and VT₄. By having $R_3 = R_2 = R_1$, VT₇ conducts the same amount of current as either VT₃ or VT₄. Assuming similar transistors and neglecting base currents, it can be shown that the diode-connected transistor VT₈ conducts the same current as that of VT₃ and VT₄. Thus they will all have equal junction drops. In this way, the emitters of VT_3 and VT_4 are held at an almost zero potential. To ensure this equality of junction drops at all environmental temperatures (as it is now guaranteed at all currents), the four transistors VT_{3,4,7,8} must be included on the same heat sink. If the circuit were integrated, this problem would be solved directly. By virtue of this additional circuit, almost complete temperature stability of the pulse generator can be achieved. It must be noted that this arrangement eliminates the offset of the control characteristic and ensures accurate frequency at the lowest control voltages (Fig. 4).

Fig. 4(a) Control characteristics for band 1 expanded to show deviations from linearity

(b) Including circuit in Fig. 6 eliminates deviations

Fig. 5 Improving output waveform by including additional transistor VT_{11}

(e) Fine tuning and digital control

If fine frequency adjustment is to be provided, another two sensitivity resistors of higher values (for example, 10 times the values of R_1 and R_2) are joined to the emitters of VT₃ and VT₄ with their other free terminals connected to another control-voltage source. This indicates the possibility of direct digital control of the frequency by supplying several pairs of binary weighted sensitivity resistors with each pair connected to the appropriate bit of the digital control signal.

Conclusions

In comparison with previous designs¹, the converter described is simple and economic. A brief discussion of the various design parameters has been given to help in arriving at an optimum design for any special requirements. Its applicability to direct digital control has also been indicated.

References

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Rci MR, Off MR, -Vec+Va

Calculation of recharging time of C_1 through output Fig. 7 resistance of VT_{s}

Appendix

Dependence of the linear-controlled frequency range on

emitter follower VT₅ used to recharge C_1 . One terminal of C_1 is clamped at $(-V_{\rm CC}+V_{\rm B})$ while the other terminal

supply voltage

From equation (1),

The minimum frequency is determined by the minimum current I required to drive both VT_1 and VT_2 into saturation; hence,

$$f_{\min} = \frac{I_{\rm C(sat)}}{2Ch_{\rm FE}V_{\rm Z}}$$

and neglecting $V_{CE(sat)}$

$$f_{\min} = \frac{V_{\rm CC}}{2Ch_{\rm FE}R_{\rm C}V_{\rm Z}} \qquad \dots \dots$$

The maximum frequency is determined by the time required to recharge the timing capacitors (recovery time). This is calculated by reference to Fig. 7, which shows the

starts from $(-V_{cc}+V_b)$ and rises until it is clamped at $(-V_{cc}+V_z)$. This time T_r is given by

$$T_{\rm r} = \frac{CR_{\rm c}}{h_{\rm FE}} \left/ \ln \frac{V_{\rm CC} - 2V_{\rm B}}{V_{\rm CC} - V_{\rm Z} - V_{\rm I}} \right|$$

Equating T_r to $T_{min}/2$, the maximum frequency is given by

$$f_{\rm max} = \frac{h_{\rm FE}}{2CR_{\rm c}} / \ln \frac{V_{\rm CC} - 2V_{\rm B}}{V_{\rm CC} - V_{\rm Z} - V_{\rm B}} \dots \dots \dots \dots (7)$$

Combining equations (6) and (7), assuming $V_{\rm B} \ll V_{\rm CC}$ and denoting $V_{\rm CC}/V_{\rm Z}$ by x, the frequency range is given by

$$f.r. = \frac{f_{\max}}{f_{\min}}$$

Therefore

f.r. =
$$\frac{h_{\rm FE}^2}{x \ln [x/(x-1)]}$$
 (5)

A value for x could be found to give the optimum frequency range by differentiation of f.r. with respect to x.

F.E.T. isolation unit for a nerve stimulator

... (6)

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A pair of f.e.t.s followed by two silicon transistors form an effective, inexpensive and easily constructed stimulus-isolation unit. The unit is suitable for use with a mains-driven stimulator for class studies of nerve in vitro.

Ein Paar Feldeffekttransistoren mit zwei nachgeschalteten Siliziumtransistoren bilden eine wirksame, leicht aufzubauende Trennschaltung für Erregerimpulse. Die Schaltung ist in Verbindung mit einem netzgespeisten Erregergerät 'geeignet für Klassenuntersuchungen von Nerven in vitro.

Une paire de transistors à effet de champ, suivie de deux transistors au silicium, constitue un ensemble d'isolement d'excitation efficace et de construction aisée. Cet ensemble peut être utilisé en liaison avec un simulateur entraîné par un courant secteur pour l'étude des nerss sous verre.

IN EXPERIMENTAL WORK, nerves are usually stimulated electrically using a squarewave pulse. Such stimulation not only initiates an action potential in the nerve fibres but transmits the stimulating potential along the bundle of nerve fibres to the recording electrodes and indicating oscilloscope. As the potential of the squarewave is usually 500mV or more, compared with some 5mV or less of action potential detected by recording electrodes outside the nerve, the stimulation artifact can be sufficient to unbalance the amplifier of the oscilloscope so that the action potential immediately following is masked. Most of this artifact can be eliminated when working with nerve in vitro, by placing an earthing electrode on the nerve between the stimulating and the recording electrodes, as is well known^{1,2} but when a mains-driven stimulator is used sufficient artifact remains after the squarewave to distort the action potential as recorded on the oscilloscope, Fig. 1. This persistent artifact is due to resistive and capa-

